



SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 055071-0329	SERIAL NO. 10/756,830	
				APPLICANT Doug van den BROEKE, et al.		
				FILING DATE January 14, 2004	GROUP 2891	
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code(s if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
<i>Come</i>		US 5,895,741	04-20-1999	Hasegawa et al.		
		US 6,214,497 B1	04-10-2001	Stanton		
		US 2002/0152452 A1	10-17-2002	Socha		
		US 5,682,323	10-28-1997	Pasch et al.		
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<i>Come</i>		US 6,223,139 B1	04-24-2001	Wong et al.		
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FOREIGN PATENT DOCUMENTS						
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes - Number - Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No
<i>Come</i>		EP 1 202 119 A1	05-02-2002	ASML Masktools B.V.	x	
<i>Come</i>		WO 03/054626 A1	07-03-2003	ADVANCED MICRO DEVICES, INC.	x	
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)						
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				
<i>Come</i>		Christoph DOLAINSKY, et al., "Simulation based method for sidelobe suppression," Optical Microlithography XIII, Proceedings of SPIE, 2000, pp 1156-1162, Vol. 4000				
		Kyoji NAKAJO, et al., "Auxiliary pattern generation to cancel unexpected images at sidelobe overlap regions in attenuated phase-shift masks,"				
		Nicolas Bailey COBB, "Fast Optical and Process Proximity Correction Algorithms for Integrated Circuit Manufacturing," Ph.D. dissertation, Spring 1998, pp 35-72, University of California at Berkeley				
		J. Fung CHEN, et al., "Practical I-Line OPC Contact Masks for Sub-0.3Micron Design Rule Application: Part 1—OPC Design Optimization," pp 181-201				
		J.A. TORRES, et al., "Contrast-Based Assist Feature Optimization," Optical Microlithography XV, 2002, pp 179-187, Proceedings of SPIE, Vol 4891, SPIE				
		Olivier TOUBLAN, et al., "Fully Automatic Side Lobe Detection and Correction Technique for Attenuated Phase Shift Masks," Optical Microlithography XIV, 2001, pp 1541-1547, Proceedings of SPIE, Vol. 4346, SPIE				
		Michael S. YEUNG, "Extension of the Hopkins theory of partially coherent imaging to include thin-film interference effects," Optical/Laser Microlithography VI, 1993, pp 452-463, SPIE, Vol. 1927				
<i>Come</i>		Douglas VAN DEN BROEKE, et al., "Near 0.3 k, Full Pitch Range Contact Hole Patterning Using Chromeless Phase Lithography (CPL)," Proceedings of the SPIE, September 9, 2003, pp 297-308, Vol. 5256, SPIE				
EXAMINER <i>C. Juerkhardt</i>			DATE CONSIDERED <i>5-15-06</i>			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

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<p style="text-align: center;"><i>OIPE FEB 21 2006 PATENT AND TRADEMARK OFFICE</i></p> <p>APPLICANT Doug van den BROEKE, et al.</p>						
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<i>CYME</i>		US 5,229,230	07/20/1993	Kamon		
<i>CYME</i>		US 5,895,741	04/20/1999	Hasegawa et al.		
<i>CYME</i>		US 6,413,684 B1	07/02/2002	Stanton		
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<i>CYME</i>		WO 02/03140 A1	01/10/2002	NUMERICAL TECHNOLOGIES, INC.		X
<i>CYME</i>		EP 1 237 046 A2	09/04/2002	ASML MASKTOOLS B.V.		X
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EXAMINER <i>C. Jaurekall</i>			DATE CONSIDERED <i>5-15-06</i>			

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